

BSO 615N

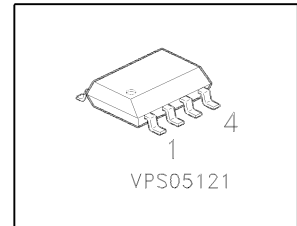
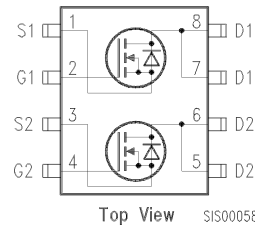
SIPMOS® Small-Signal-Transistor

Features

- Dual N Channel
- Enhancement mode
- Avalanche rated
- Logic Level
- dv/dt rated

Product Summary

Drain source voltage	V_{DS}	60	V
Drain-Source on-state resistance	$R_{DS(on)}$	0.15	Ω
Continuous drain current	I_D	2.6	A



Type	Package	Ordering Code
BSO 615N	SO 8	Q67041-S2843

Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current, <i>one channel active</i>	I_D	2.6	A
Pulsed drain current, <i>one channel active</i>	I_{Dpulse}	10.4	
$T_A = 25\text{ °C}$			
Avalanche energy, single pulse	E_{AS}	60	mJ
$I_D = 2.6\text{ A}$, $V_{DD} = 25\text{ V}$, $R_{GS} = 25\text{ }\Omega$			
Avalanche current, periodic limited by T_{jmax}	I_{AR}	2.6	A
Avalanche energy, periodic limited by T_{jmax}	E_{AR}	0.18	mJ
Reverse diode dv/dt	dv/dt	6	kV/ μ s
$I_S = 2.6\text{ A}$, $V_{DS} = 40\text{ V}$, $di/dt = 200\text{ A}/\mu$ s, $T_{jmax} = 150\text{ °C}$			
Gate source voltage	V_{GS}	± 20	V
Power dissipation, <i>one channel active</i>	P_{tot}	2	W
$T_A = 25\text{ °C}$			
Operating temperature	T_j	-55 ... +150	°C
Storage temperature	T_{stg}	-55 ... +150	
IEC climatic category; DIN IEC 68-1		55/150/56	